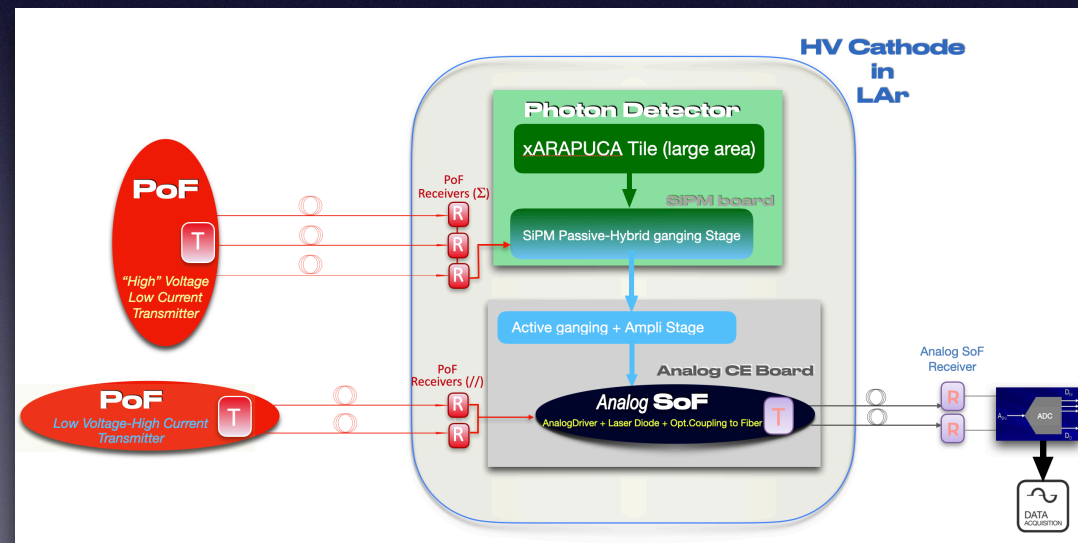


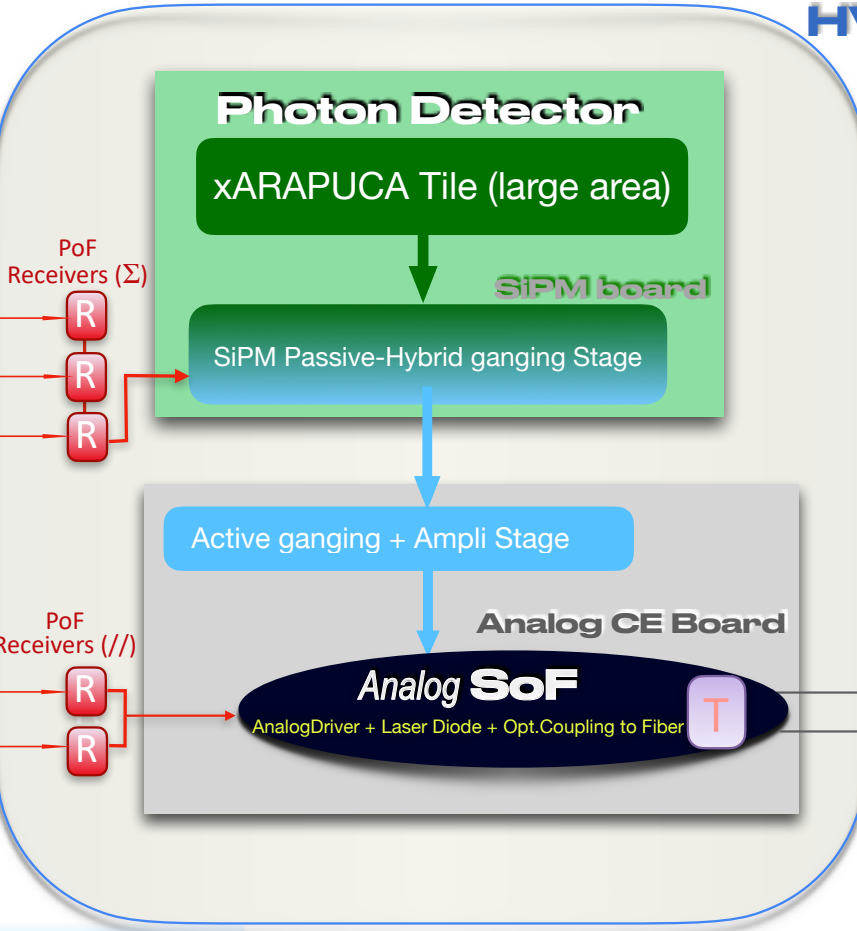
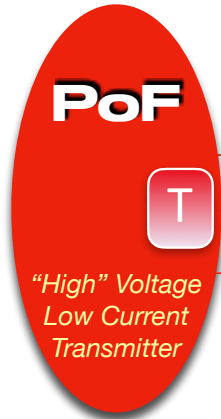
# PoF and overall Detector Design, Development and Optimization



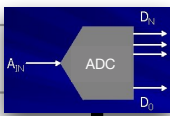
# The VD LArPDS Development path

for an electrically isolated  
(only optically connected through fibers)  
low noise  
new photon detector concept

HV Cathode  
in  
LAr



Analog SoF Receiver



... to success !!

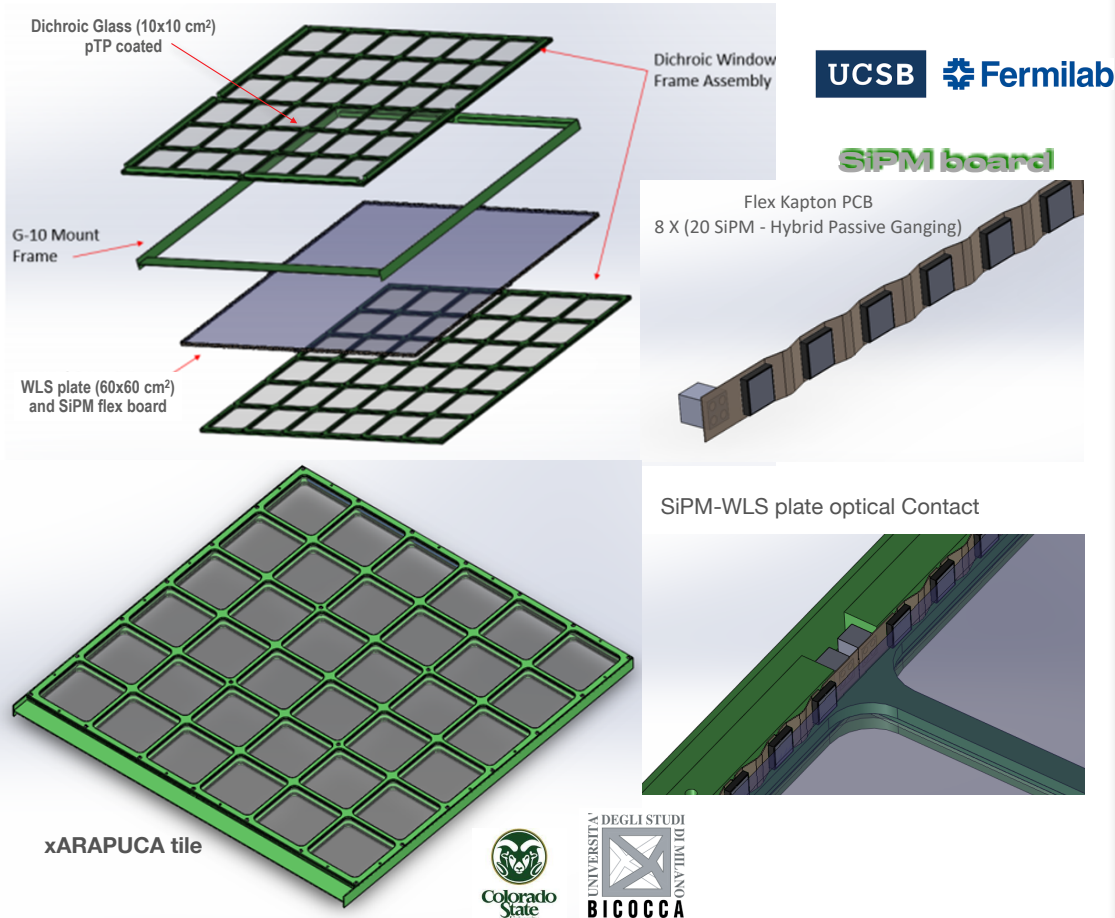


## 3 + 1 main items on the VD PDS path for development & optimization:

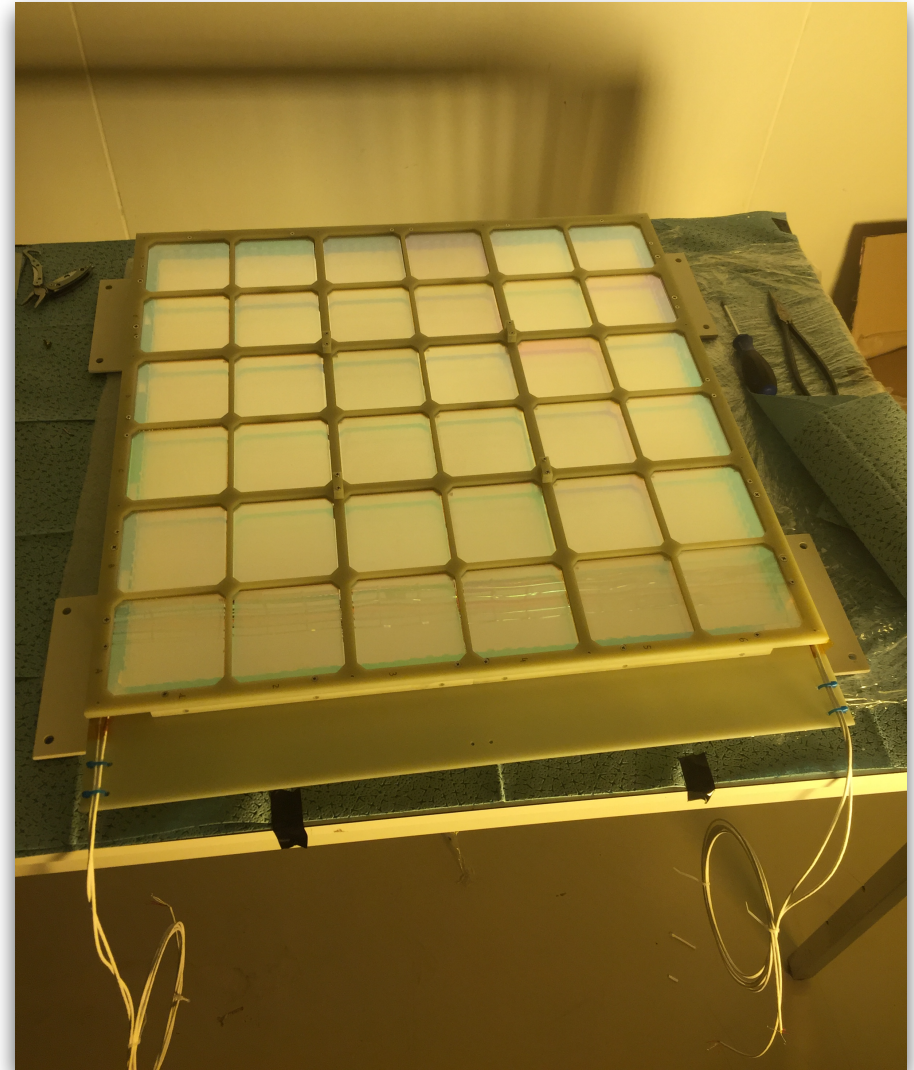
- ✦ the **large area PD module**, based on the ARAPUCA technology, with 160 SiPM/channel in 8 groups of 20 passively ganged in a hybrid Series/Parallel solution (**SiPM ganging board**).
- ✦ the **PoF system** for power supply to sensors and to r/o electronics:
  - ☆ **HV-LC PoF** for SiPMs, that require  $\mathcal{O}(< 10 \mu\text{W})$  power output, at high voltage (30-50 V) and very low current ( $< 100 \text{ nA}$  per sensor).
  - ☆ **LV-HC PoF** for OpAmps and other active analog electronics components, that require  $\mathcal{O}(> 10 \text{ mW})$ , at low voltage (3-5 V) and high current ( $> 10 \text{ mA}$  per unit).
- ✦ the **FrontEnd Cold Electronics** (SiPM Active Sum and Amplification) + **SoF system** for signal transmission out of the Cathode (toward digitization and DAQ)
- the PDS layout on the Cathode (i.e. PD modules distribution on the Cathode, Power distribution to PD modules/CE boards): **Risk mitigation for HV cathode discharge and for long term operation** (30 yrs lifetime)

# PhotoCollector concept

xARAPUCA technology - large detection Area, 2 r/o channels



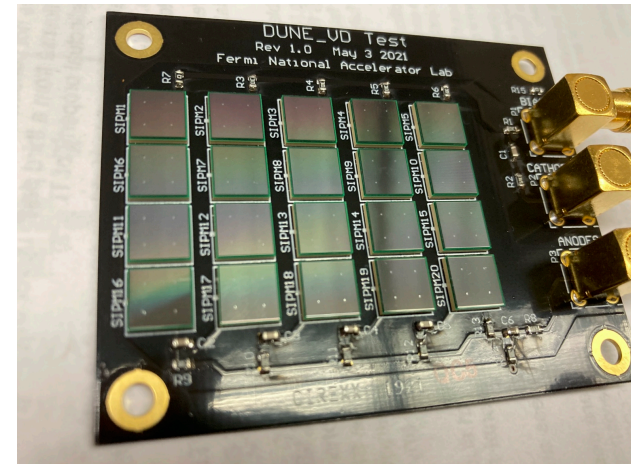
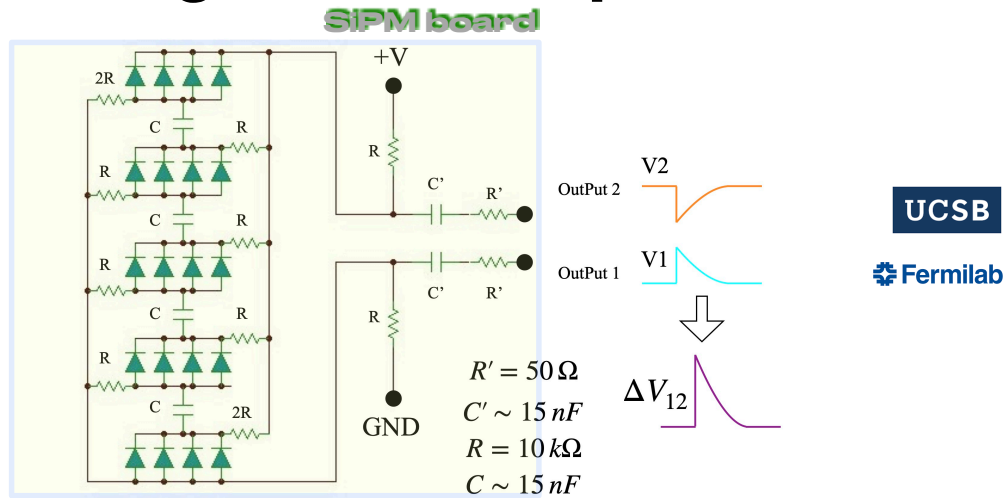
xARAPUCA tile assembled and cabled



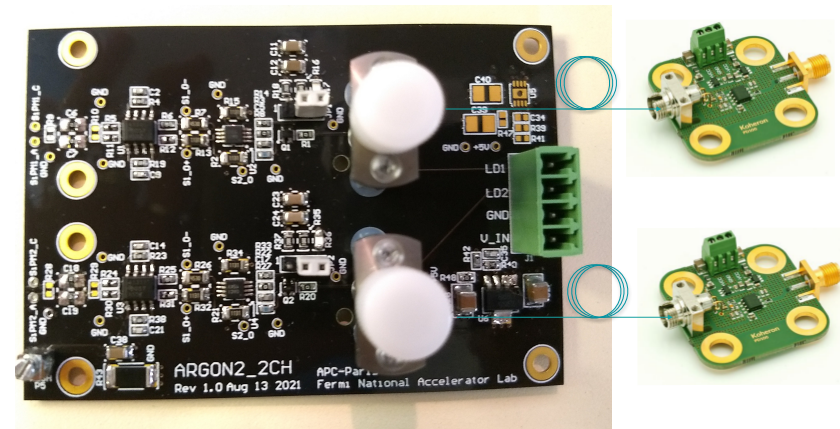
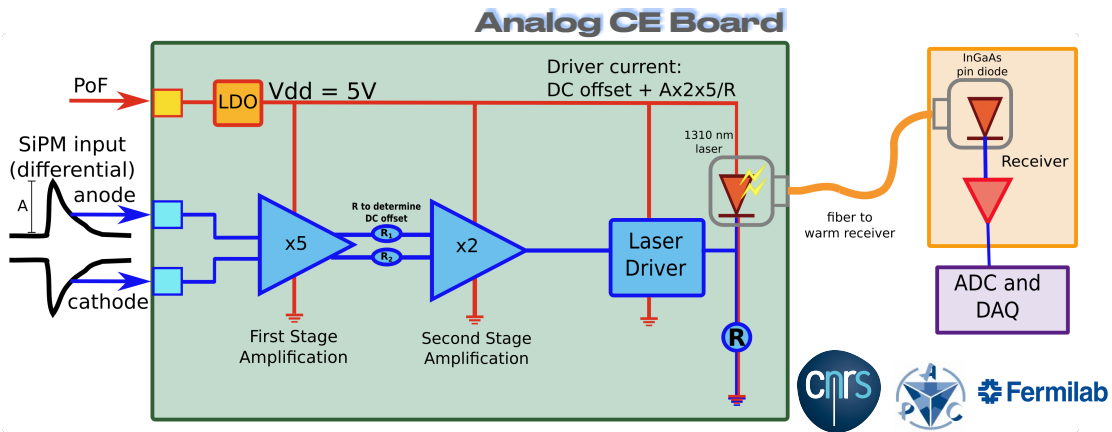
xARAPUCA tile



# Analog SoF concept



the SiPM Board(s)- Passive hybrid ganging



the Analog CE Board  
Active ganging/Ampli & SoF



# PoF concept

multimode fiber with FC connector



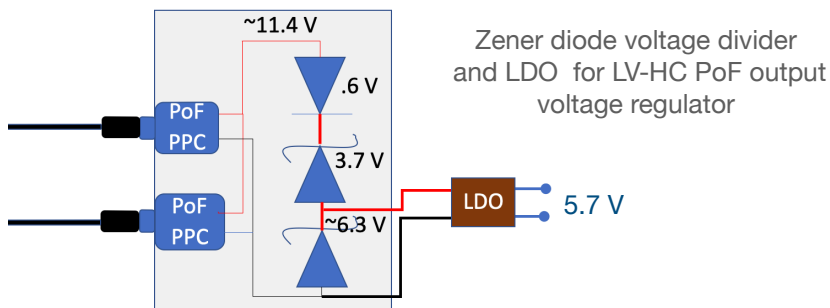
Fermilab/AD

PoF Transmitter

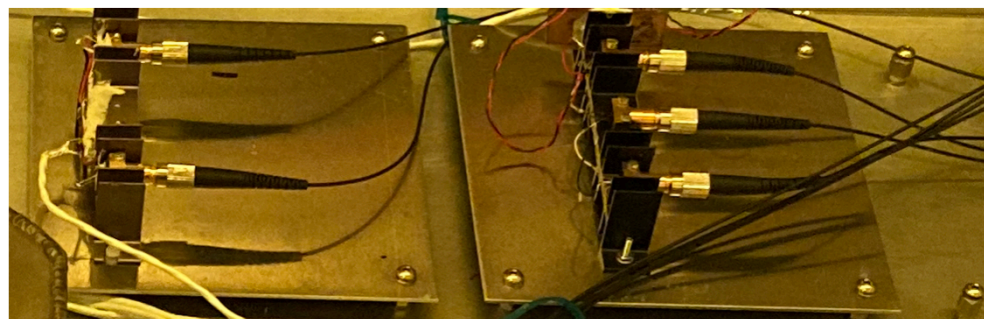
*Photonic Power Module (PPM)*  
976 nm laser diode

PoF Receiver high intensity

*Photovoltaic Power Converter (PPC)*  
on heatsink



PoF - Power housing unit (5 warm Transmitter laser diodes)



LV-HC PoF supply board  
(2 cold Receivers on heatsink)

HV-LC PoF supply cold board  
(3 cold Receivers on heatsink)

**PoF technology was developed primarily for implementation in solar energy industry and small isolated electrical systems.**

**In our application, *the first in detector technology for HEP*, PoF supplies power to the active elements, *photo-sensors and cold electronics*, of a photon detection system immersed in LAr and lying on a HV surface.**

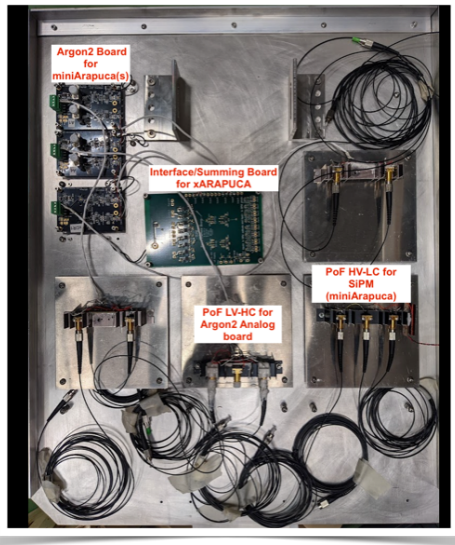
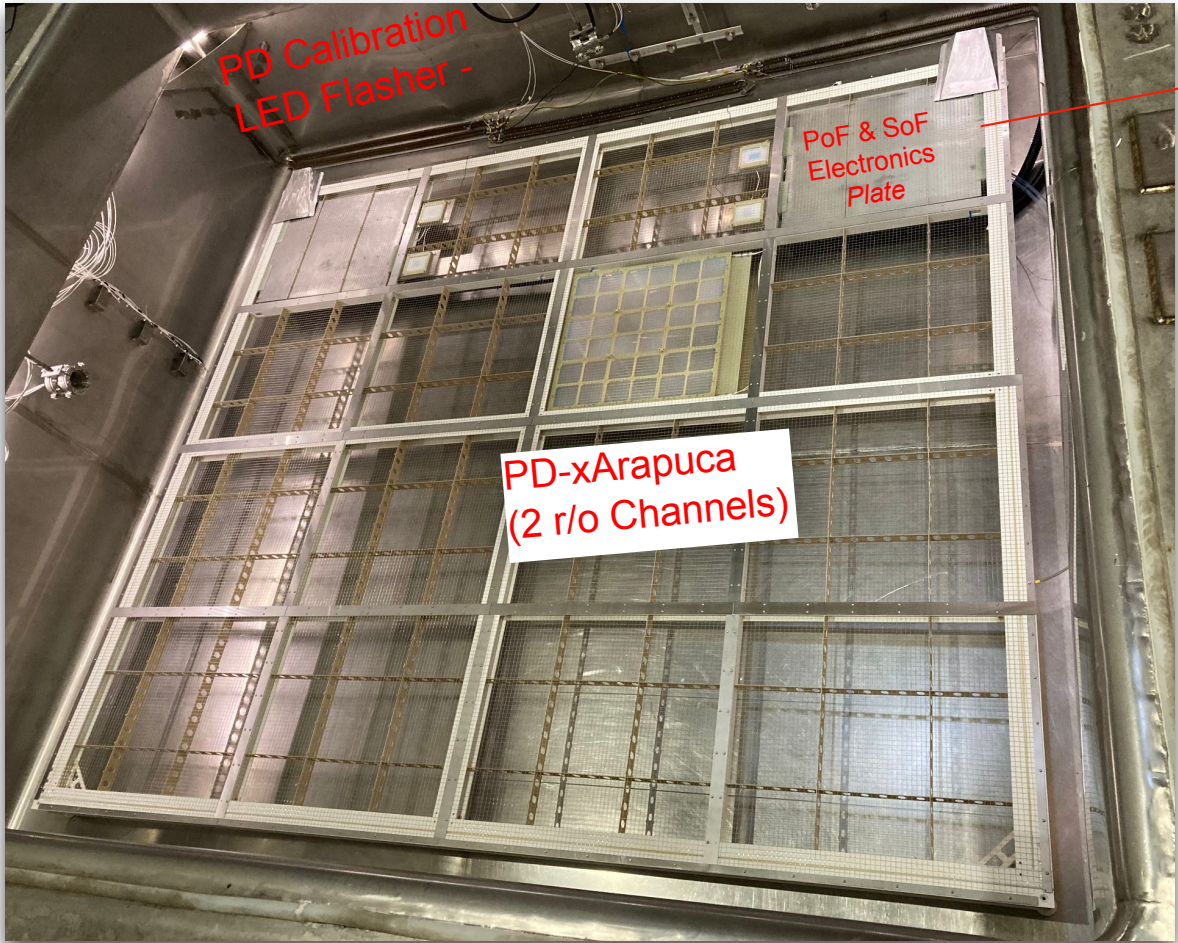
**The 976 nm, 3.5 W Si-based solution is demonstrated.**

**A new 808 nm, 3 W very high efficiency GaAs PPC units is under development/test.**

**The innovative cold PoF-SoF technology is immune from noise injection and signal distortion, and therefore adequate for low amplitude light signal collection and read-out**

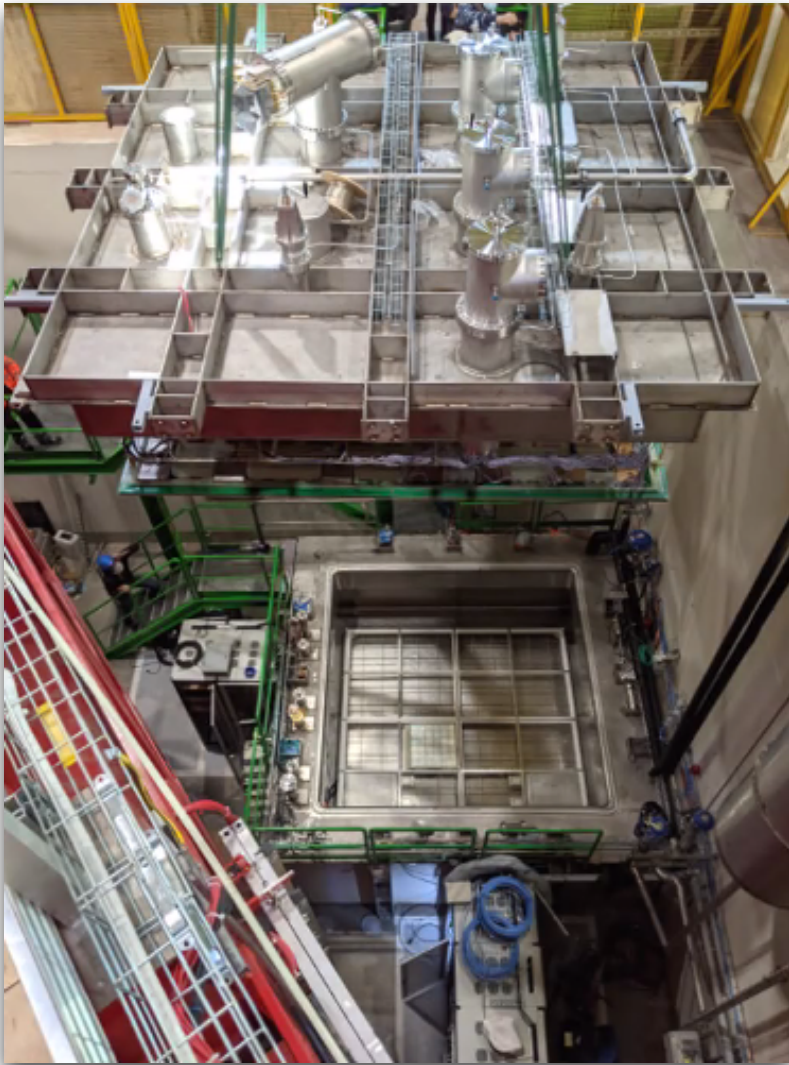


**Validation Test at CERN - NP (ColdBox experiment)**



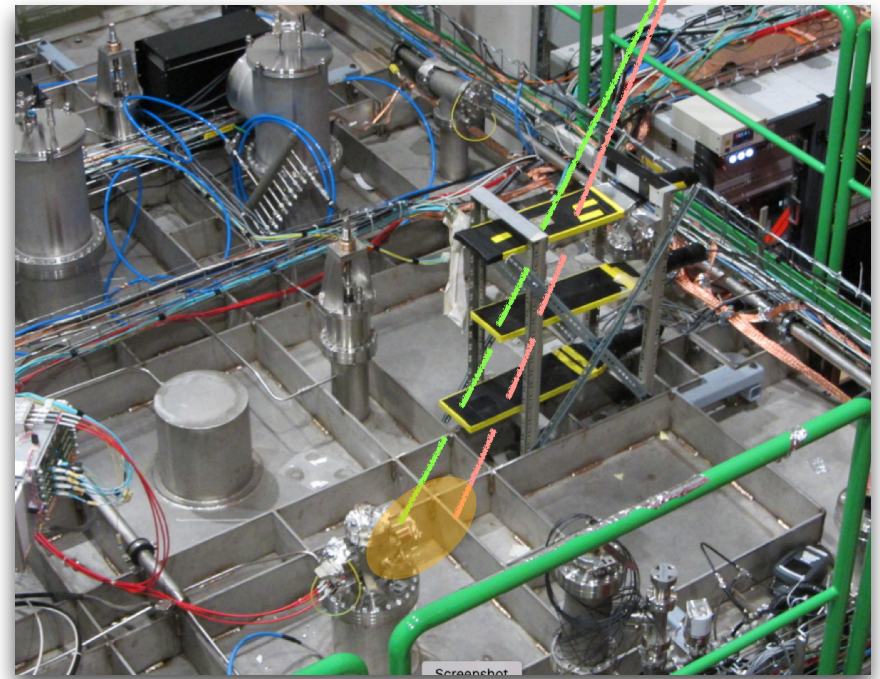
**On Dec. 13  
PDS on the Cathode + LED Calibration system  
installed in ColdBox at CERN Neutrino  
Platform**



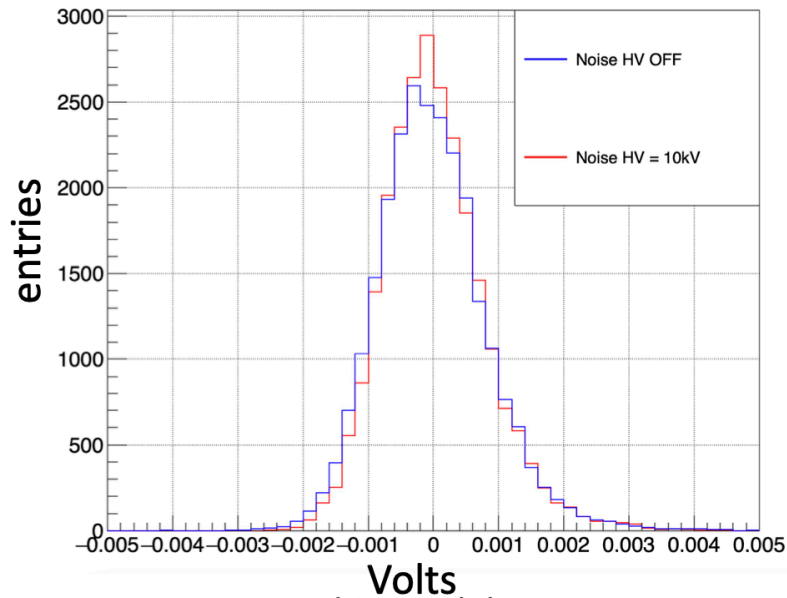


External Muon Telescope on the CB top

Cosmic Muons



No noise increase  
or signal distortion  
when HV ON



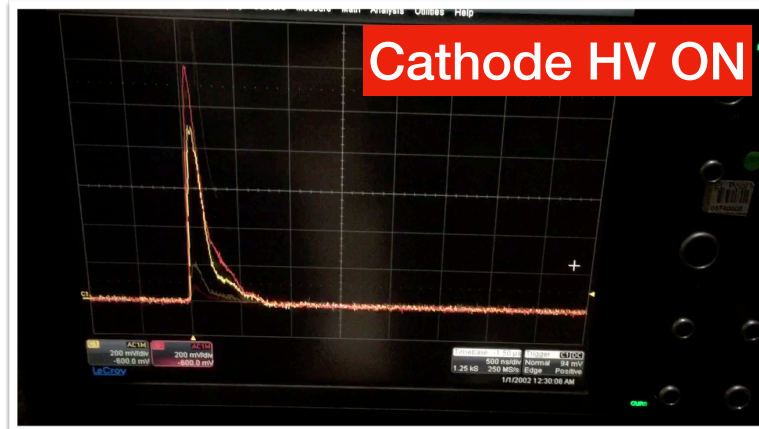
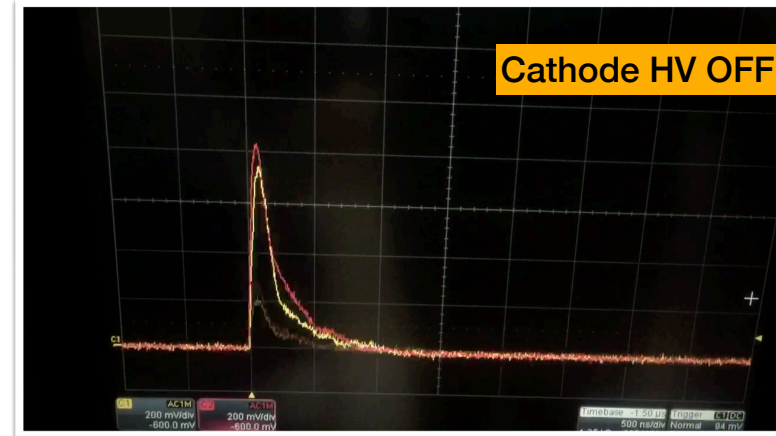
## Milestone:

PoF is turned ON  
on Dec. 15 at  
CERN - ColdBox  
Experiment. Clean  
signals immediately  
seen on scope

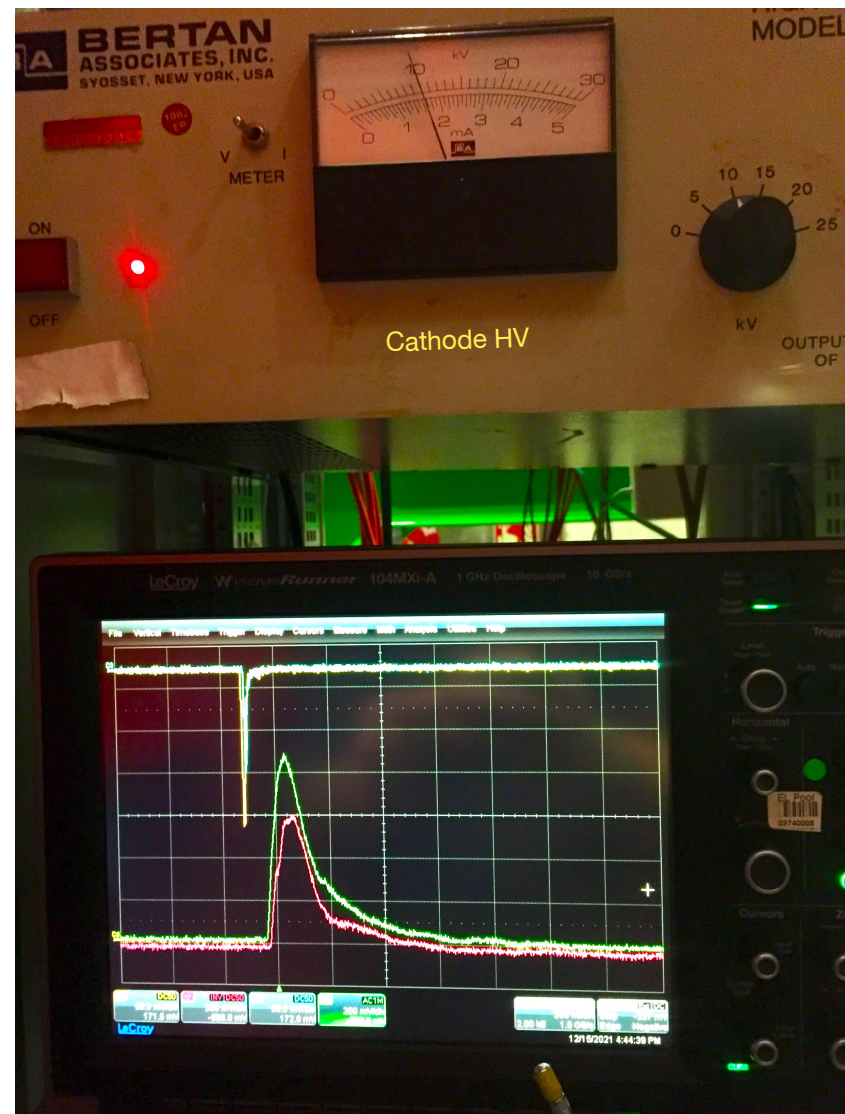
HV OFF:  
Mean = -0.05 mV  
Sigma = 0.77 mV

HV = 10 kV  
Mean = -0.02 mV  
Sigma = 0.71 mV

## VD PDS signals with Cathode HV ON in LAr







## Milestone #2:

**xARAPUCA on Cathode**  
**provide trigger to TPC DAQ and**  
**detect tracks in coincidence with Light Flash**

Collection

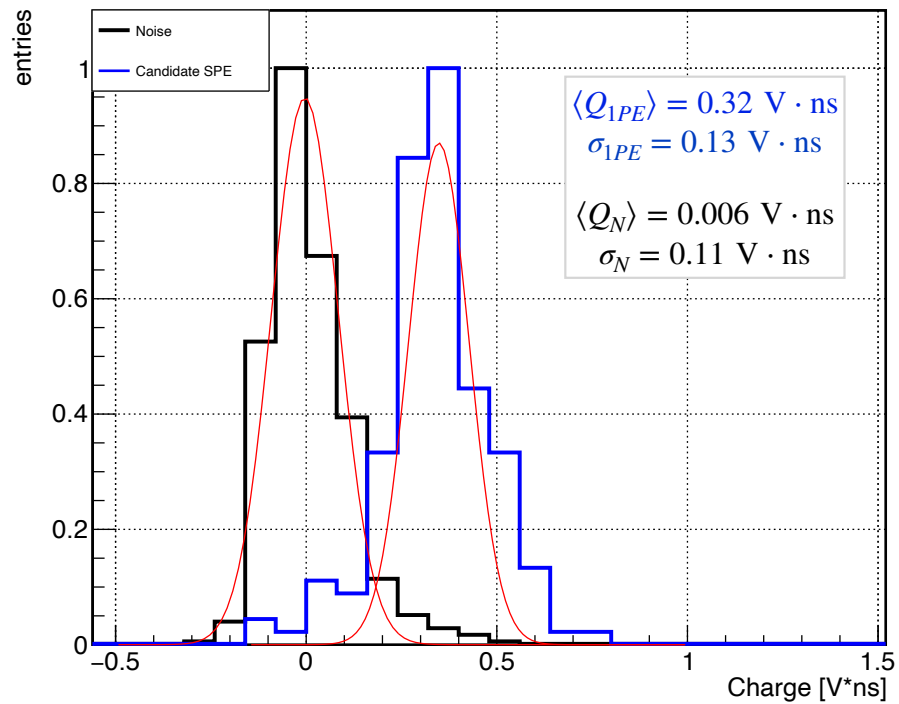
Triggered Track



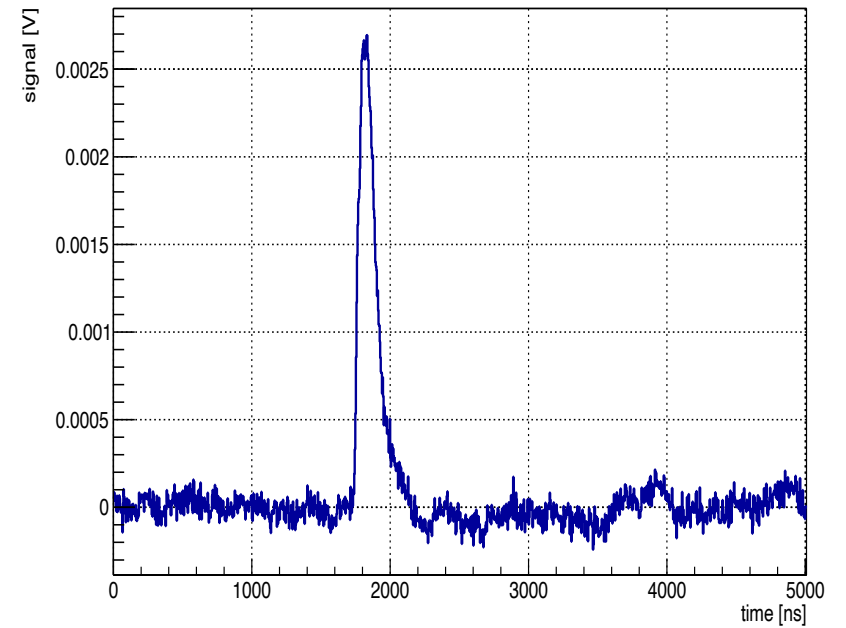


## Calibration Run

### Integral Charge



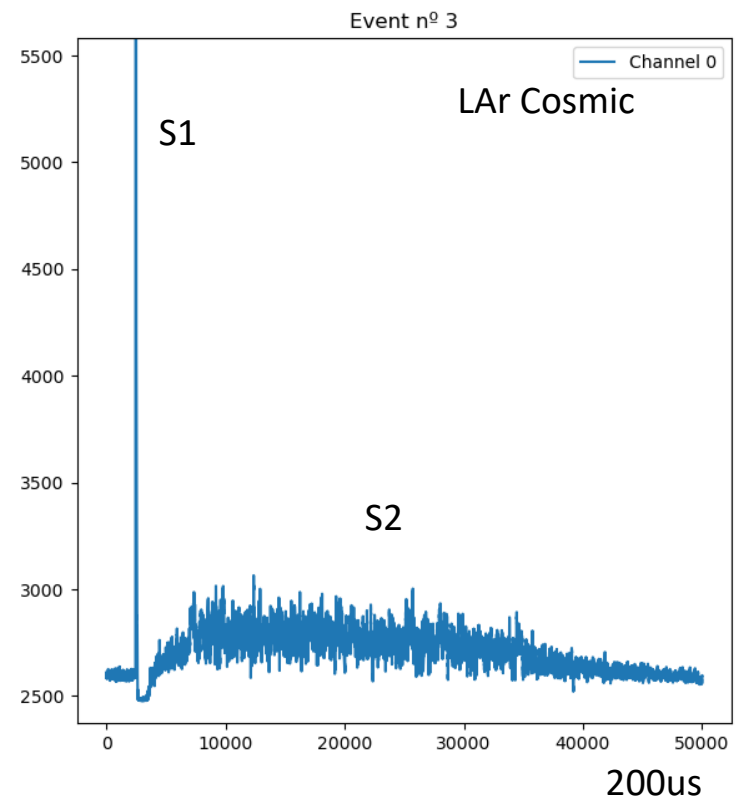
### Average SPE waveform



Noise (0-PE) and 1-PE Charge distributions (normalized)

# X-Arapuca operated during the ARIADNE LarTPC test providing S1 and S2 light signal

- X-Arapucas work nicely !



**... more on the PoF system:  
moving to 808nm  
GaAs PPC**

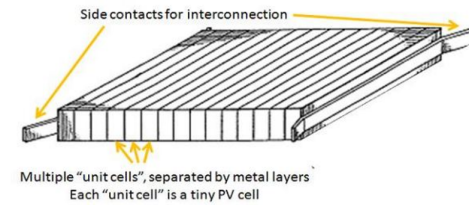
by W. Pellico / FNAL



# History

- From white board idea to VD baseline in ~2.5 years
- The use of PoF has been used in some application here at the lab
  - (small and low power at 'room' temps)
  - Used to power electronics on RF modulator HV deck
  - Used to power some electronics on FNAL transformer yard
- High power outdoor systems being built for military systems
- This first of a kind PoF use of high power in a cryo environment
  - Not a big market
  - Not many vendors

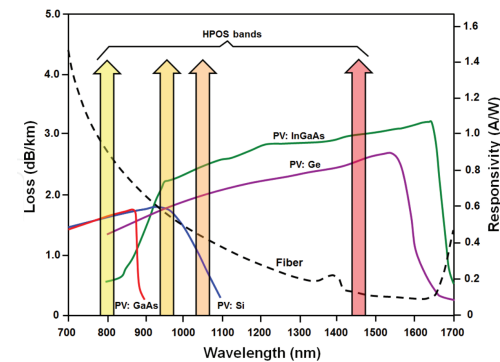
# We chose to focus on the Photovoltaic converter biggest concern was power/efficiency



- The VD cathode PD system has been a moving target
  - Power levels have change continuously –
    - We had digital Tx for a long time
    - Analog has moved to the front with power levels that have been drastically reduced
  - Layouts are still changing –
  - Initially we were also planning on FC mounted PD systems (may still happen....)
  - Localized heating – bubbles
- Our original power estimates were about a factor of 10 higher than now

**Fibers and Lasers seemed less of a vulnerability –**

**We set up several vendor / university relationships to focus on**



# PC R&D partnerships

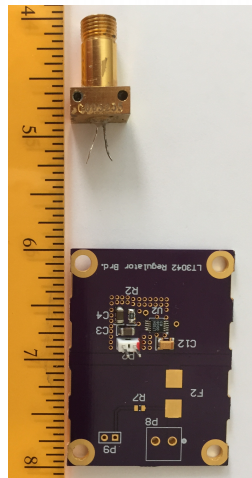
## Proof of Principle

Desire to start with a low-cost option to start the investigation. We reached out to several vendors – only one was interested in participating in R&D of PoF MH GoPower –

The company participated in initial testing at their site with nitrogen to see if it worked. We then started a series of tests with their Si based product.

The layout and components were tested over about 1.5 years. The system of lasers, fibers and PC units has become our baseline design. The president of the company visited and remain a source of expertise.

Si Based System



GaAs Based System

Initial focus on ~808nm based power systems

Broadcom

Boeing Spectrolab

UIUC Champaign Urbana

- The big vendors have extensive PC knowledge
  - Space Tech Use
- Manufacturing capabilities
- Wafer Options (2", 4" and 6")
- Fiber connectivity

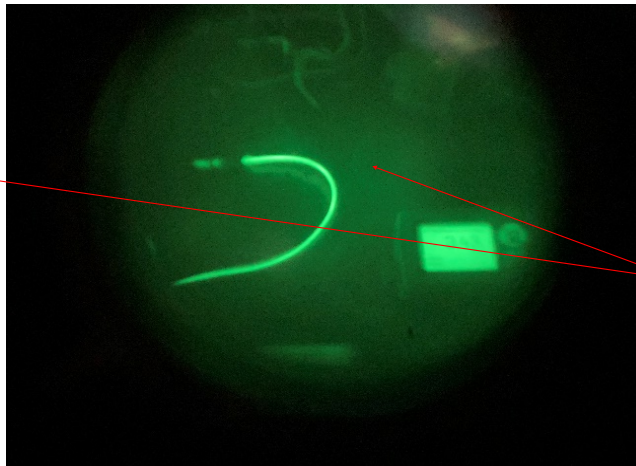
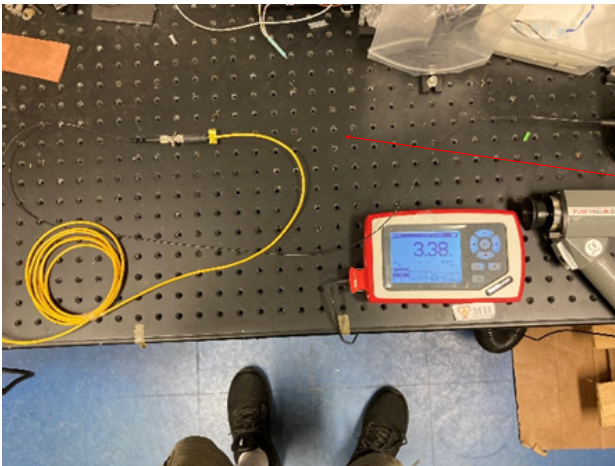
- Solar R&D Profs
- Students
- Cost
- Desire for R&D
- Accessible Lab
- Accessible Tech

We have a testing program underway with South Dakota School of Mines and Technology led by David Martinez Caicedo Ph.D.  
- This will allow FNAL to focus on R&D



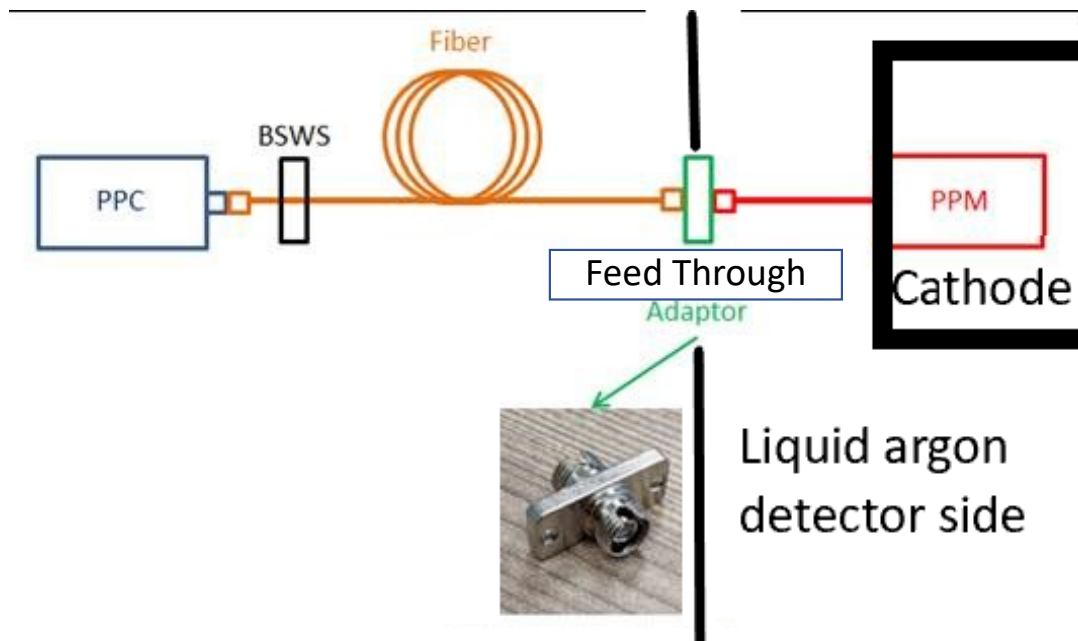
# Si Based PoF System

- We have had a lot of success with Si PoF but some growing pains
  - Lasers systems are fairly robust – but we have gone through 4 versions
    - Have had vendor modify some connectors – especially at pigtail
    - Interlocks needed upgrading
    - Simplification of dim connector – simplified unit
  - PPC cells have been good with only 10% loss during testing
    - Issues with stripping of connector teeth – quality issue
    - Light leakage from backside due to semi-opaque epoxy
  - Initial fiber jacket was not light tight



Pigtail fiber leaks So MUST Use:  
Black 1.5mm PVDF jacket, Black  
1.8mm ETFE jacket

# Si PoF System Proven to Meet VD PD Needs



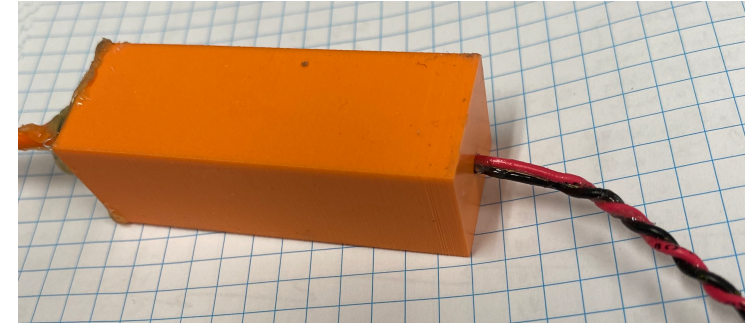
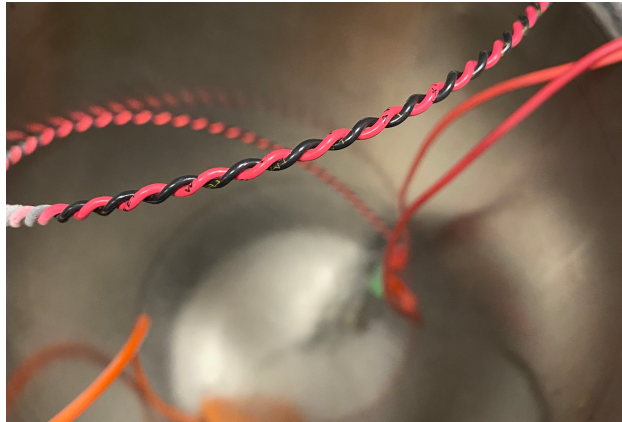
- Successful conclusion of CB1
- Proof of Principle
  - System proved to be low noise
  - Once system is installed it is reliable and repeatable
  - Simple to operate
  - Laser power was reduced
  - No bubbles
  - Not impacted by HV system

# So Why Go Beyond what we did at CB1

- The Si based system will have limited efficiency at cryo temps –
- Even at room temps Si is not the best option for high power
- The desire to reach efficiencies of >50%, maybe up > 85% possible
  
- Theory says for a single wavelength a GaAs system can reach ~90 % efficiency
- Lasers Systems are lower cost – (not a big driver)



## First set of 808nm GaAs System Testing



**GaAs Unit powering an Argonx2 board.**  
PC inside small box filled with silicon sealant.  
Running at 1.1 W laser power.  
Slightly better than Si but room for improvement.



Clear low VOC Si sealant (-173c)



## 808 nm Laser Systems

and new Laser and new converter (Teflon jacket) from Broadcom.

# Upcoming CB2 Testing

808nm C - Lasers

808nm B - Lasers

105um fiber

105 fiber feedthrough (3 fibers)

62.5 fiber feedthrough (Use 1 spare)

2.5 Fiber Power

Broadcom 62.5um fiber 808 nm light (may get Wed)



PoF LV-HC

FNAL silicon2 potted

PoF HV-LC

Copper Power

48V SiPM 20

35 V SiPM 20

Dc-Dc Stepup

35 V SiPM 4

New mini-XARAPUCAs

35 V SiPM 20

Fermi Made Arapuca

SoF Ch2 A6 SoF Ch1  
Argonx2  
In Place at CERN

SoF Ch2 Good SoF Ch1  
Argonx2  
Use old mixed Tx

6 V

6 V

FNAL silicon1 potted

PoF LV-HC

Fiber#2

Fiber#3

Pigtail white Fiber#0

Fiber#1

Red

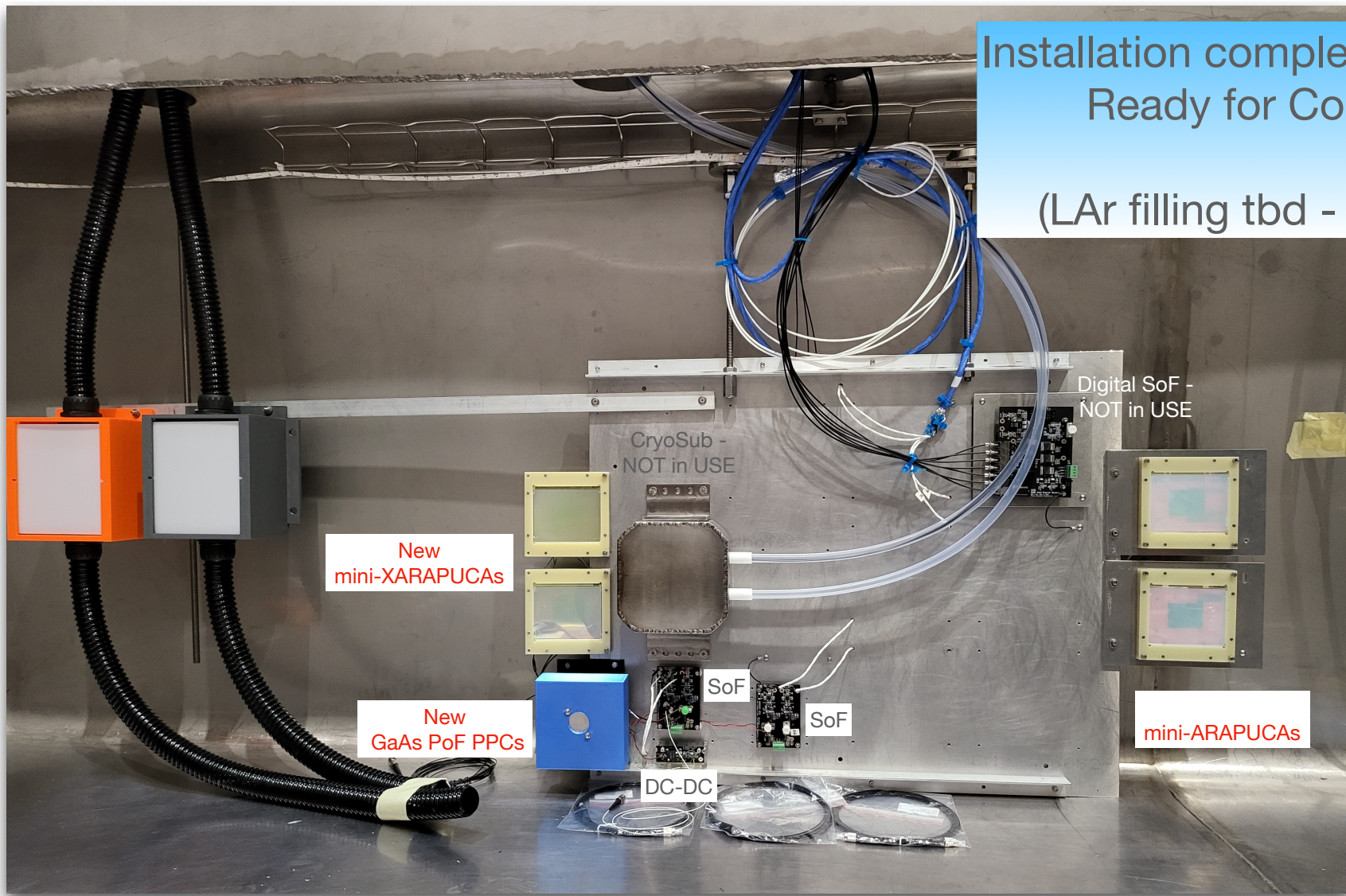
Black

Gray/Beige

Yellow

Broadcom Teflon Unit





Installation completed on Apr.27  
Ready for ColdBox#2  
(LAr filling tbd - ~mid May)

New mini-XARAPUCAs

New GaAs PoF PPCs

DC-DC

SoF

SoF

CryoSub - NOT in USE

Digital SoF - NOT in USE

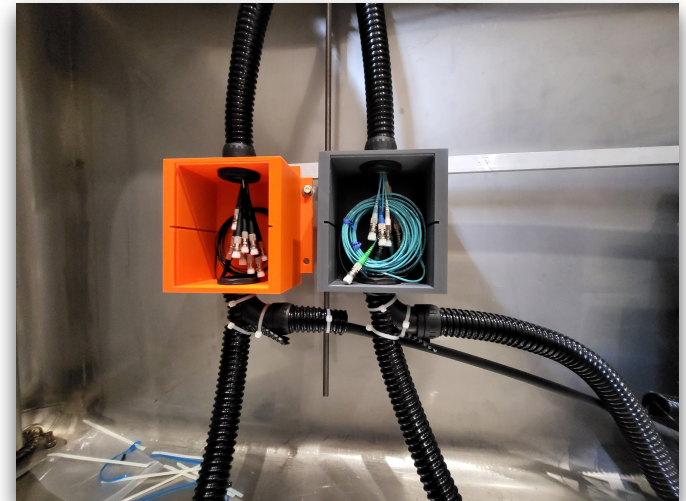
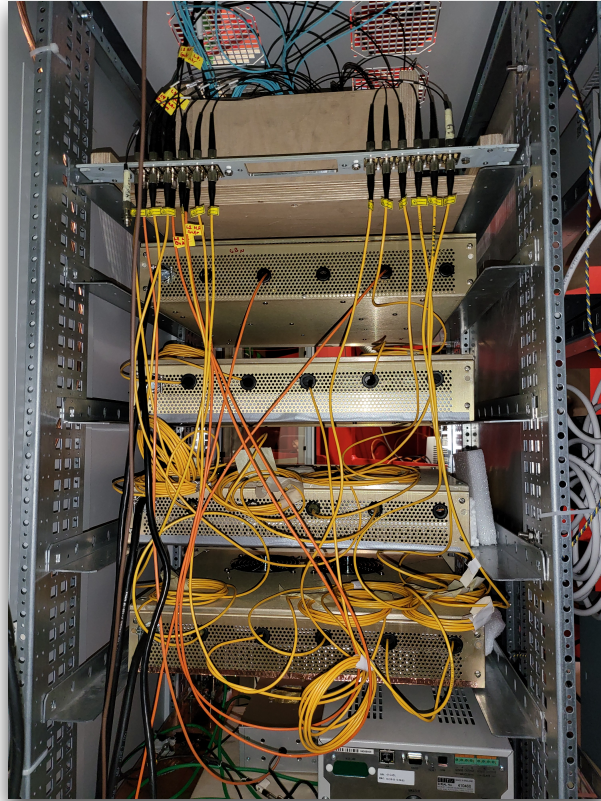
mini-ARAPUCAs





New  
808nm Laser Box  
3 PPM units

New  
808nm Laser  
PPM (Broadcom)



## Upcoming PC R&D – At the Semiconductor Level

Looking to improve fill factor at cryo temps

Looking to reduce  $R_s$

Looking to find a way to size up design/semiconductor

Present efficiency in cryo at ~51 % - Will do better

# New LPC Design to Lower Series Resistance ( $R_S$ )

- Design

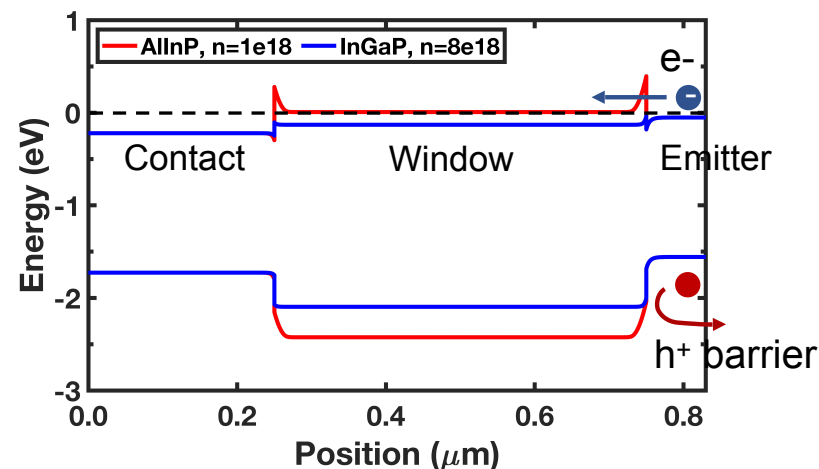
- #1  $\longrightarrow$  • #3

Au/Ti
n-GaAs contact
20nm n-AlInP window, $n=1e18$
50nm n-GaAs emitter, $n=1e18$
2um p-GaAs base, $p=1e17$
50nm p-GaAs base I, $p=2e18$
50nm p-InGaP BSF, $p=1e18$
200nm p-GaAs buffer, $p=7e18$
600nm p-GaAs substrate
Au/Cr

Au/Ti
n-GaAs contact
TiO <sub>2</sub> /SiO <sub>2</sub> DLARC
500nm n-InGaP window, $n=8e18$
80nm n-GaAs emitter, $n=1e18$
2um p-GaAs base, $p=1e17$
100nm p-GaAs BSF, $p=7e18 \rightarrow 1e17$
400nm p-GaAs buffer, $p=7e18$
600nm p-GaAs substrate
Au/Cr

- Aspects expected to be improved

- Low  $R_S$  enabled by thick, n+-InGaP
- Suppressed majority carrier blocking



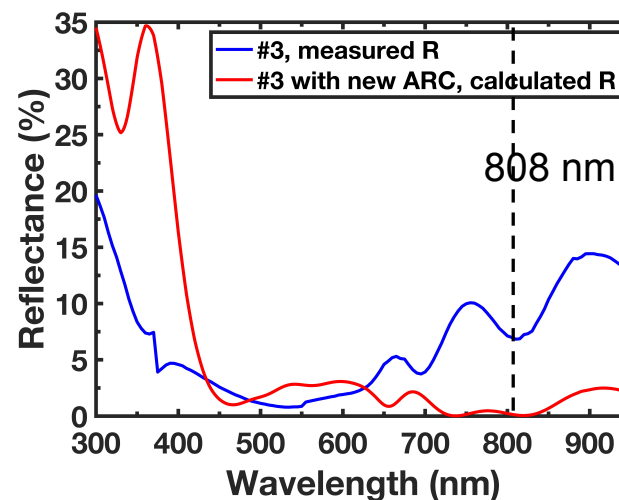
- Low  $R_{sheet}$  (33-35 ohm/sq)
- EQE enhancement by DLARC



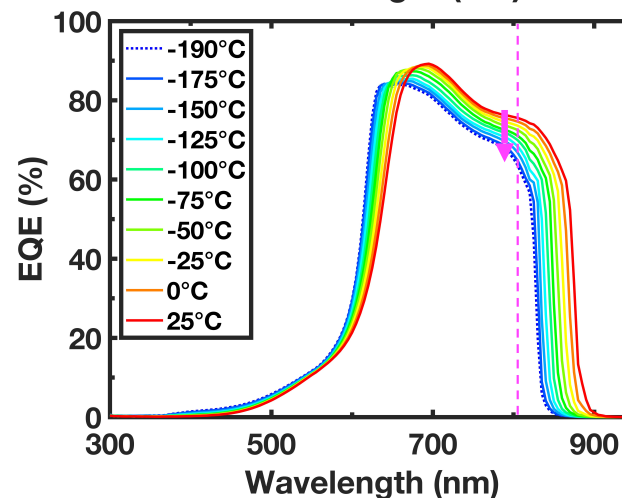
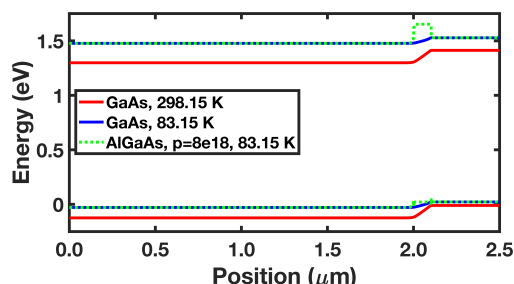
# Near-Term Roadmap for 60% Efficiency GaAs LPC at Low T

- **EQE boost with optimized ARC**
- Simply, with optimum ARC, efficiency at 190 °C will be  $\uparrow$  to ~54%.

ID	R <sub>808 nm</sub> at RT	EQE <sub>808 nm</sub> at RT	EQE <sub>808 nm</sub> at -190 °C
#3	7.0%	75.4%	62.2%
#3 with optimum ARC	0.2%	80.9%*	66.8%*



- **p+Al<sub>0.1</sub>GaAs BSF**
- Diffusion length  $\uparrow$ , barrier for minority carrier
- $\rightarrow$  suppress decrease in EQE at low T



**Following the successful Validation Test at CERN ColdBox#1 in Dec.21 and the continued operation during the ARIADNE ColdBox test in Feb/Mar 22**

**PDS with PoF&SoF is now baselined for DUNE FD2**

**PDS with PoF&SoF is currently in its optimization phase (2022-23)**

**ProtoDUNE-VD Module-0 Integration Test (2023) milestone for final approval**

**PDS Construction phase expected starting in 2024.**

**A large international community of groups/institutions from DUNE PD Consortium engaged for PDS realization**

**PDS ColdElectronics primary scope for US/DoE**

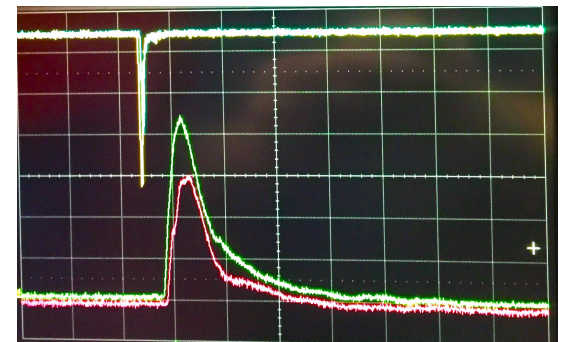
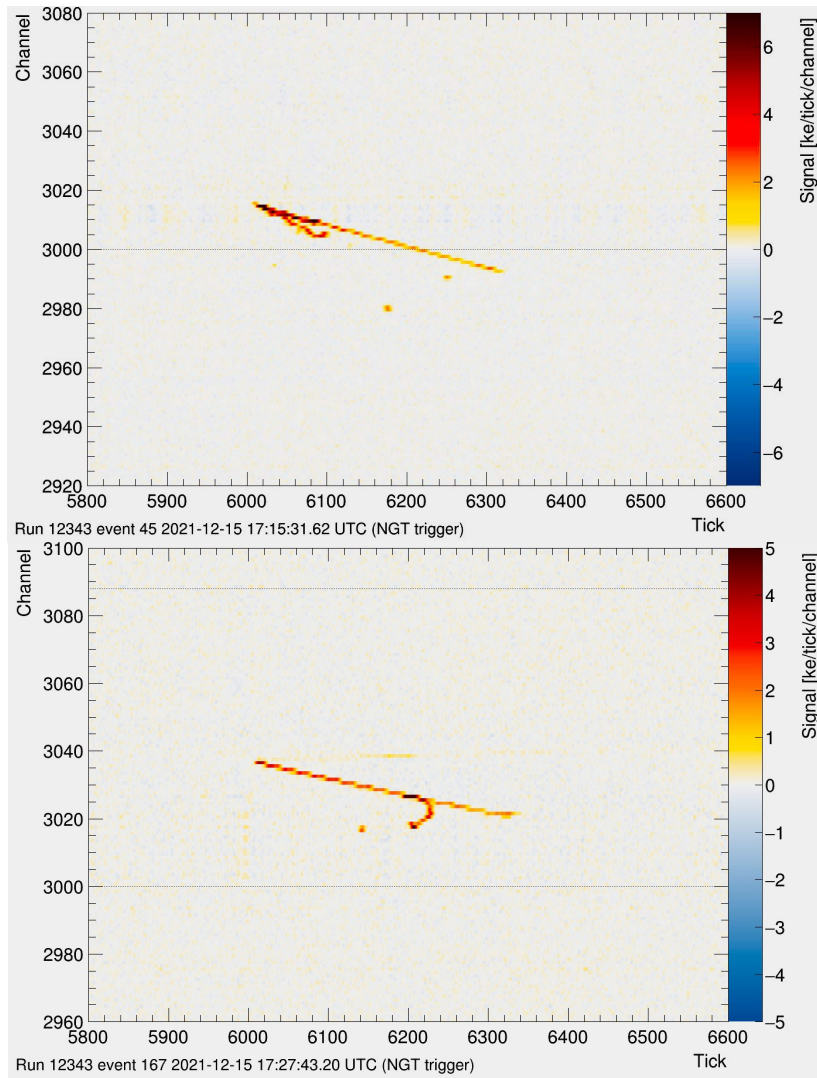
**+ important contributions from EU groups**

**FERMILAB leading institution, with Project management responsibility**

**CE optimization and Detector design finalization on the critical path**

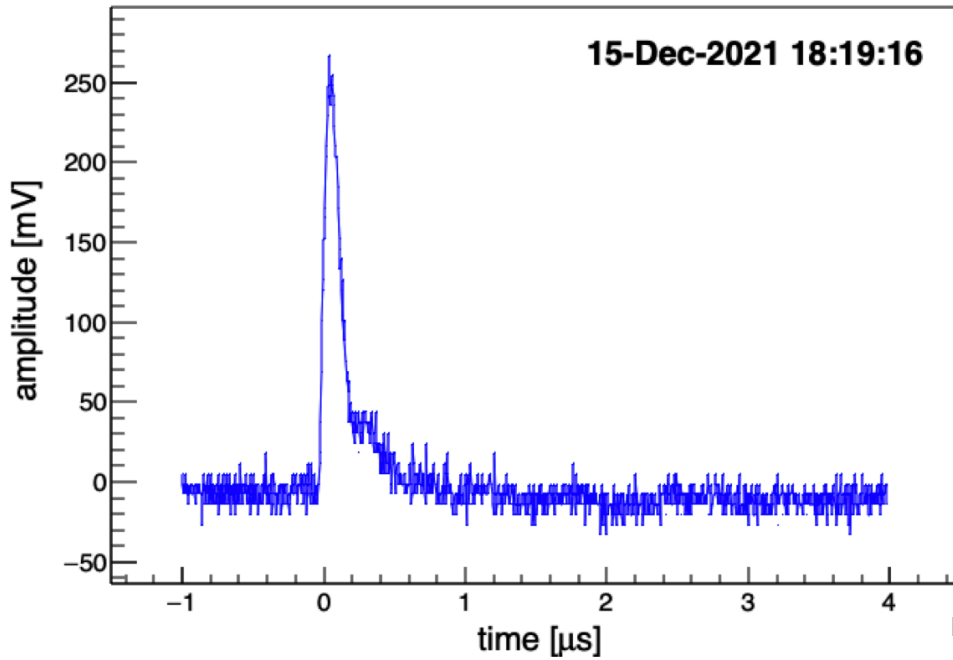
BackUp





# Example of signals triggered on CRT + X-Arapuca

X-Arapuca Ch1



X-Arapuca Ch2

